

## **ABSTRACT**

A method for improving hot carrier effects in complementary metal oxide semiconductor (CMOS) devices includes forming a first configuration of insulating material over a first group of the CMOS devices, and forming a second configuration of insulating material over a second group of the CMOS devices. The first and said second configurations of insulating material are formed subsequent to a silicidation of the CMOS devices and prior to formation of a first interlevel (ILD) dielectric material over the CMOS devices.